

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**LISTING OF CLAIMS:**

Claims 1-14 (canceled).

Claim 15 (new): A branching filter comprising:

a transmitting filter; and

a receiving filter; wherein

piezoelectric thin film resonators including at least one piezoelectric thin film sandwiched between at least one pair of opposed electrodes are arranged in a ladder configuration on an opening or a recess of a substrate, the transmitting filter and the receiving filter being connected to an antenna terminal in parallel; and

the piezoelectric thin film resonators defining the transmitting filter and the piezoelectric thin film resonators defining the receiving filter have a different structure from each other.

Claim 16 (new): The branching filter according to claim 15, wherein the piezoelectric thin film resonators defining the transmitting filter and the piezoelectric thin film resonators defining the receiving filter have different piezoelectric films.

Claim 17 (new): The branching filter according to claim 16, wherein the piezoelectric film of the piezoelectric thin film resonators defining the transmitting filter

includes AlN and the piezoelectric film of the piezoelectric thin film resonators defining the receiving filter includes ZnO.

Claim 18 (new): The branching filter according to claim 15, wherein the material of the electrodes is different between the piezoelectric thin film resonators defining the transmitting filter and the piezoelectric thin film resonators defining the receiving filter.

Claim 19 (new): The branching filter according to claim 18, wherein the acoustic impedance of the material of the electrodes is different between the piezoelectric thin film resonators defining the transmitting filter and the piezoelectric thin film resonators defining the receiving filter.

Claim 20 (new): The branching filter according to claim 18, wherein the frequency of the pass band of the receiving filter is higher than the frequency of the pass band of the transmitting filter, and the acoustic impedance of the material of the electrodes defining the receiving filter is higher than the acoustic impedance of the material of the electrodes defining the transmitting filter.

Claim 21 (new): The branching filter according to claim 15, wherein the piezoelectric thin film resonators defining the transmitting filter use second harmonic waves and the piezoelectric thin film resonators defining the receiving filter use fundamental waves.

Claim 22 (new): The branching filter according to claim 15, wherein the piezoelectric thin film resonators defining the transmitting filter and the piezoelectric thin film resonators defining the receiving filter further comprise a different insulating film on the opening or the recess of the substrate.

Claim 23 (new): The branching filter according to claim 22, wherein the insulating film of the piezoelectric thin film resonators defining the receiving filter comprises SiO<sub>2</sub>.

Claim 24 (new): The branching filter according to claim 22, wherein the insulating film of the piezoelectric thin film resonators defining the receiving filter comprises two layers including an SiO<sub>2</sub> layer adjacent to the piezoelectric thin film and an Al<sub>2</sub>O<sub>3</sub> layer adjacent to the SiO<sub>2</sub> layer.

Claim 25 (new): The branching filter according to claim 22, wherein the insulating film of the piezoelectric thin film resonators defining the receiving filter comprises two layers including an SiO<sub>2</sub> layer adjacent to the piezoelectric thin film and an AlN layer adjacent to the SiO<sub>2</sub> layer.

Claim 26 (new): The branching filter according to claim 22, wherein the insulating film of the piezoelectric thin film resonators defining the transmitting filter comprises two layers including an AlN layer adjacent to the piezoelectric thin film and an SiO<sub>2</sub> layer adjacent to the AlN layer.

Claim 27 (new): The branching filter according to claim 22, wherein the insulating film of the piezoelectric thin film resonators defining the transmitting filter comprises two layers including an  $\text{Al}_2\text{O}_3$  layer adjacent to the piezoelectric thin film and an  $\text{SiO}_2$  layer adjacent to the  $\text{Al}_2\text{O}_3$  layer.

Claim 28 (new): A communication device comprising the branching filter according to claim 15.